MC14013B

Dual Type D Flip-Flop

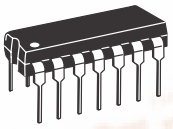
The MC14013B dual type D flip–flop is constructed with MOS P–channel and N–channel enhancement mode devices in a single monolithic structure. Each flip–flop has independent Data, (D), Direct Set, (S), Direct Reset, (R), and Clock (C) inputs and complementary outputs (Q and $\overline{Q}$). These devices may be used as shift register elements or as type T flip–flops for counter and toggle applications.

- Static Operation
- Diode Protection on All Inputs
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Logic Edge–Clocked Flip–Flop Design
  Logic state is retained indefinitely with clock level either high or low; information is transferred to the output only on the positive–going edge of the clock pulse
- Capable of Driving Two Low–power TTL Loads or One Low–power Schottky TTL Load Over the Rated Temperature Range
- Pin–for–Pin Replacement for CD4013B

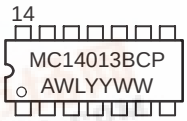
ON Semiconductor

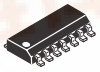
http://onsemi.com

MARKING DIAGRAMS

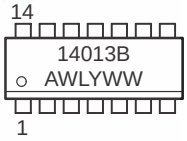


PDIP–14
P SUFFIX
CASE 646

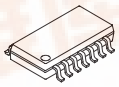




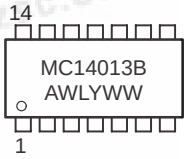
SOIC–14
D SUFFIX
CASE 751A



TSSOP–14
DT SUFFIX
CASE 948G



SOEIAJ–14
F SUFFIX
CASE 965



A = Assembly Location
WL or L = Wafer Lot
YY or Y = Year
WW or W = Work Week

MAXIMUM RATINGS (Voltages Referenced to V_{SS}) (Note 2.)

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	–0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	–0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 3.)	500	mW
T_A	Ambient Temperature Range	–55 to +125	°C
T_{stg}	Storage Temperature Range	–65 to +150	°C
T_L	Lead Temperature (8–Second Soldering)	260	°C

2. Maximum Ratings are those values beyond which damage to the device may occur.
3. Temperature Derating:
   Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

ORDERING INFORMATION

Device	Package	Shipping
MC14013BCP	PDIP–14	2000/Box
MC14013BD	SOIC–14	55/Rail
MC14013BDR2	SOIC–14	2500/Tape & Reel
MC14013BDT	TSSOP–14	96/Rail
MC14013BDTR2	TSSOP–14	2500/Tape & Reel
MC14013BF	SOEIAJ–14	See Note 1.
MC14013BFEL	SOEIAJ–14	See Note 1.

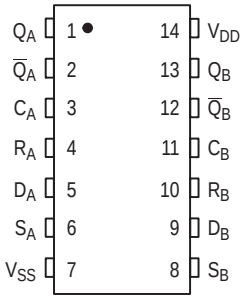
1. For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

TRUTH TABLE

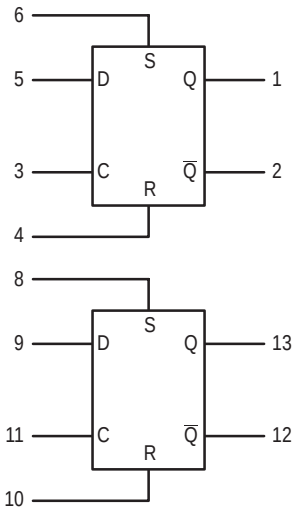
Inputs				Outputs		
Clock†	Data	Reset	Set	Q	$\overline{Q}$	
⎍	0	0	0	0	1	
⎍	1	0	0	1	0	
⎎	X	0	0	Q	$\overline{Q}$	No Change
X	X	1	0	0	1	
X	X	0	1	1	0	
X	X	1	1	1	1	

X = Don't Care
† = Level Change

PIN ASSIGNMENT



BLOCK DIAGRAM



V_{DD} = PIN 14
V_{SS} = PIN 7

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ (4.)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	— — —	0.05 0.05 0.05	— — —	0 0 0	0.05 0.05 0.05	— — —	0.05 0.05 0.05	Vdc
V_{in} = 0 or V_{DD} “1” Level	V_{OH}	5.0 10 15	4.95 9.95 14.95	— — —	4.95 9.95 14.95	5.0 10 15	— — —	4.95 9.95 14.95	— — —	Vdc
Input Voltage “0” Level (V_O = 4.5 or 0.5 Vdc) (V_O = 9.0 or 1.0 Vdc) (V_O = 13.5 or 1.5 Vdc)	V_{IL}	5.0 10 15	— — —	1.5 3.0 4.0	— — —	2.25 4.50 6.75	1.5 3.0 4.0	— — —	1.5 3.0 4.0	Vdc
(V_O = 0.5 or 4.5 Vdc) “1” Level (V_O = 1.0 or 9.0 Vdc) (V_O = 1.5 or 13.5 Vdc)	V_{IH}	5.0 10 15	3.5 7.0 11	— — —	3.5 7.0 11	2.75 5.50 8.25	— — —	3.5 7.0 11	— — —	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) Source (V_{OH} = 4.6 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	I_{OH}	5.0 5.0 10 15	– 3.0 – 0.64 – 1.6 – 4.2	— — — —	– 2.4 – 0.51 – 1.3 – 3.4	– 4.2 – 0.88 – 2.25 – 8.8	— — — —	– 1.7 – 0.36 – 0.9 – 2.4	— — — —	mAdc
(V_{OL} = 0.4 Vdc) Sink (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	I_{OL}	5.0 10 15	0.64 1.6 4.2	— — —	0.51 1.3 3.4	0.88 2.25 8.8	— — —	0.36 0.9 2.4	— — —	mAdc
Input Current	I_{in}	15	—	± 0.1	—	±0.00001	± 0.1	—	± 1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	— — —	1.0 2.0 4.0	— — —	0.002 0.004 0.006	1.0 2.0 4.0	— — —	30 60 120	µAdc
Total Supply Current (5.) (6.) (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0 10 15	I_T = (0.75 µA/kHz) f + I_{DD} I_T = (1.5 µA/kHz) f + I_{DD} I_T = (2.3 µA/kHz) f + I_{DD}							µAdc

4. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
5. The formulas given are for the typical characteristics only at 25°C.
6. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

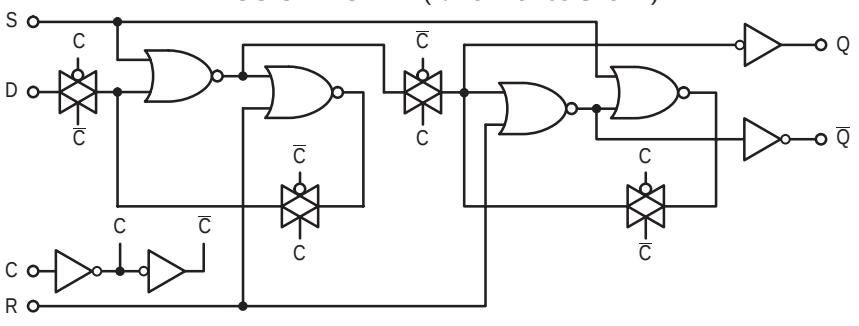
where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.002.

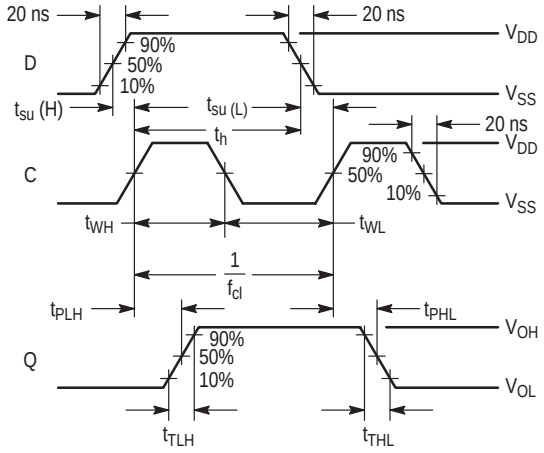
SWITCHING CHARACTERISTICS [7.] (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD}	Min	Typ [8.]	Max	Unit
Output Rise and Fall Time	t_{TLH},					ns
t_{TLH}, t_{THL} = (1.5 ns/pF) C_L + 25 ns	t_{THL}	5.0	—	100	200	
t_{TLH}, t_{THL} = (0.75 ns/pF) C_L + 12.5 ns		10	—	50	100	
t_{TLH}, t_{THL} = (0.55 ns/pF) C_L + 9.5 ns		15	—	40	80	
Propagation Delay Time	t_{PLH}					ns
Clock to Q, $\overline{Q}$	t_{PHL}					
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 90 ns		5.0	—	175	350	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 42 ns		10	—	75	150	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 25 ns		15	—	50	100	
Set to Q, $\overline{Q}$						
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 90 ns		5.0	—	175	350	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 42 ns		10	—	75	150	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 25 ns		15	—	50	100	
Reset to Q, $\overline{Q}$						
t_{PLH}, t_{PHL} = (1.7 ns/pF) C_L + 265 ns		5.0	—	225	450	
t_{PLH}, t_{PHL} = (0.66 ns/pF) C_L + 67 ns		10	—	100	200	
t_{PLH}, t_{PHL} = (0.5 ns/pF) C_L + 50 ns		15	—	75	150	
Setup Times [9.]	t_{su}	5.0	40	20	—	ns
		10	20	10	—	
		15	15	7.5	—	
Hold Times [9.]	t_h	5.0	40	20	—	ns
		10	20	10	—	
		15	15	7.5	—	
Clock Pulse Width	t_{WL}, t_{WH}	5.0	250	125	—	ns
		10	100	50	—	
		15	70	35	—	
Clock Pulse Frequency	f_{cl}	5.0	—	4.0	2.0	MHz
		10	—	10	5.0	
		15	—	14	7.0	
Clock Pulse Rise and Fall Time	t_{TLH}	5.0	—	—	15	μs
	t_{THL}	10	—	—	5.0	
		15	—	—	4.0	
Set and Reset Pulse Width	t_{WL}, t_{WH}	5.0	250	125	—	ns
		10	100	50	—	
		15	70	35	—	
Removal Times	t_{rem}					ns
Set		5	80	0	—	
		10	45	5	—	
		15	35	5	—	
Reset		5	50	– 35	—	
		10	30	– 10	—	
		15	25	– 5	—	

7. The formulas given are for the typical characteristics only at 25°C.
8. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
9. Data must be valid for 250 ns with a 5 V supply, 100 ns with 10 V, and 70 ns with 15 V.

LOGIC DIAGRAM (1/2 of Device Shown)





Inputs R and S low.

Figure 1. Dynamic Signal Waveforms (Data, Clock, and Output)

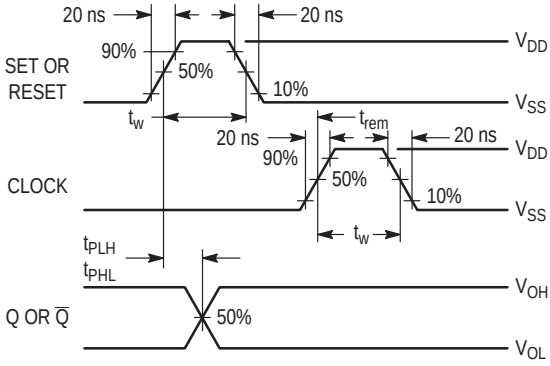
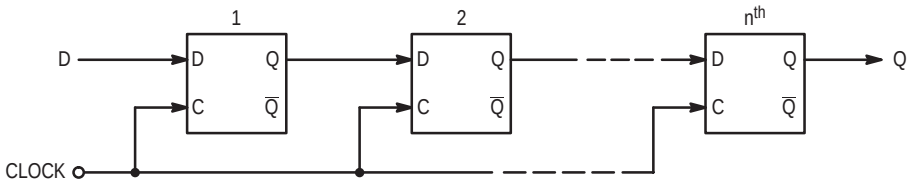


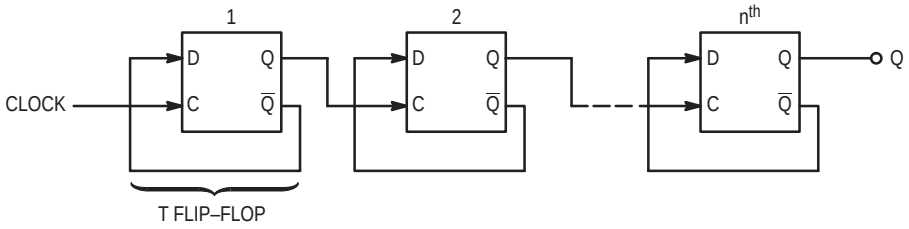
Figure 2. Dynamic Signal Waveforms (Set, Reset, Clock, and Output)

TYPICAL APPLICATIONS

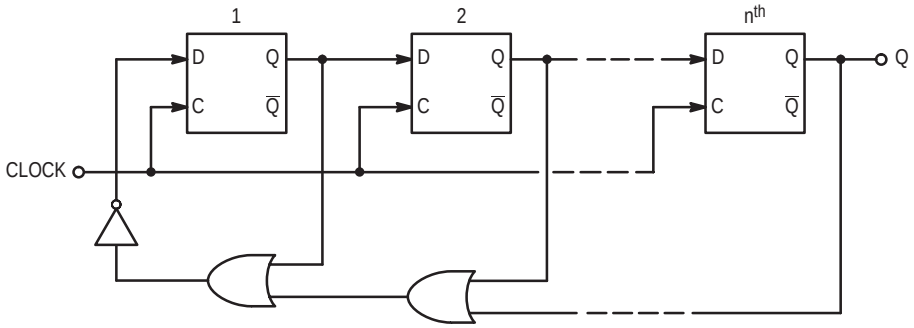
n–STAGE SHIFT REGISTER



BINARY RIPPLE UP–COUNTER (Divide–by–2^n)

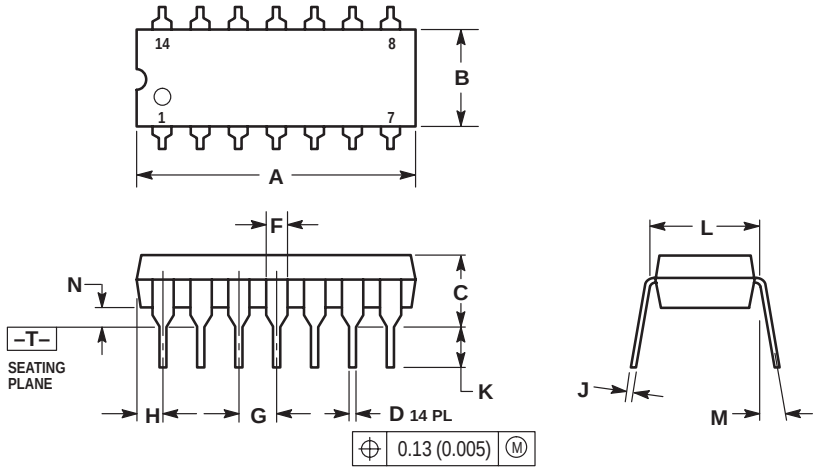


MODIFIED RING COUNTER (Divide–by–(n+1))



PACKAGE DIMENSIONS

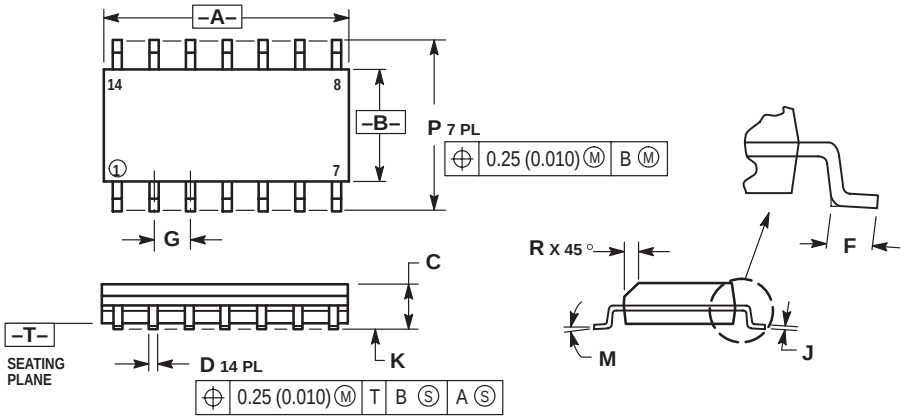
P SUFFIX
PLASTIC DIP PACKAGE
CASE 646–06
ISSUE M



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	18.80
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	—	10°	—	10°
N	0.015	0.039	0.38	1.01

D SUFFIX
PLASTIC SOIC PACKAGE
CASE 751A–03
ISSUE F

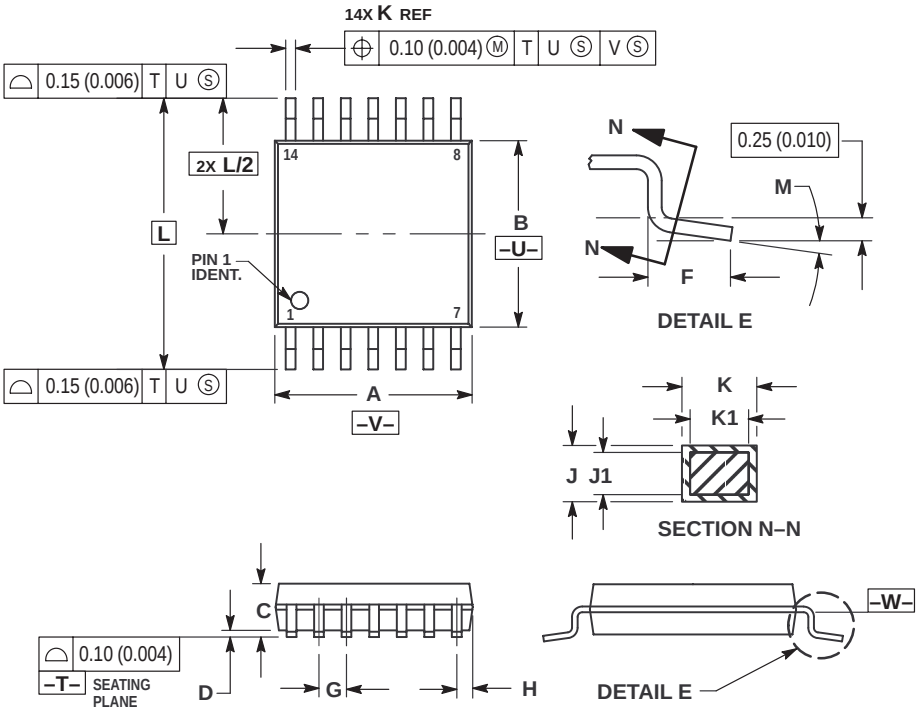


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

PACKAGE DIMENSIONS

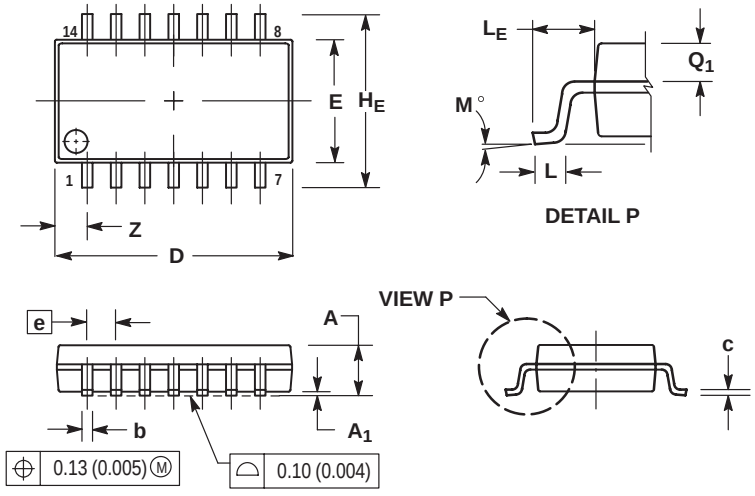
DT SUFFIX
PLASTIC TSSOP PACKAGE
CASE 948G–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	—	1.20	—	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

F SUFFIX
PLASTIC EIAJ SOIC PACKAGE
CASE 965–01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	—	2.05	—	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	—	1.42	—	0.056

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